Features

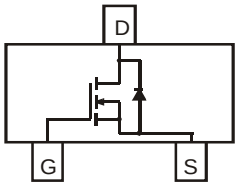
- Low On-Resistance
  - 110 mΩ @ V_{GS} = 4.5V
  - 145 mΩ @ V_{GS} = 2.5V
  - 230 mΩ @ V_{GS} = 1.8V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 1, 2 and 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.008 grams (approximate)

SOT23

Top View



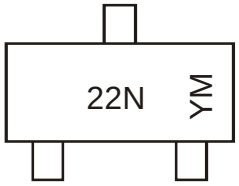
Top View
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2230U-7	SOT23	3000/Tape & Reel

Notes: 1. No purposefully added lead. Halogen and Antimony Free.
2. Product manufactured with Green Molding Compound and does not contain Halogens or Sb_2O_3 Fire Retardants.

Marking Information



22N = Marking Code
YM = Date Code Marking
Y = Year (ex: U = 2007)
M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	20	V
Gate-Source Voltage	V_{GSS}	±12	V
Drain Current (Note 5)	I_D	2.0	A
Pulsed Drain Current (Note 6)	I_{DM}	7	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	600	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	208	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±10	μA	V_{GS} = ±12V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	—	1.0	V	V_{DS} = V_{CS}, I_D = 250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	81 113 170	110 145 230	mΩ	V_{GS} = 4.5V, I_D = 2.5A V_{GS} = 2.5V, I_D = 1.5A V_{GS} = 1.8V, I_D = 1.0A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	5	—	S	V_{DS} = 5V, I_D = 2.4A
Diode Forward Voltage (Note 7)	V_{SD}	—	0.8	1.1	V	V_{GS} = 0V, I_S = 1.05A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	188	—	pF	V_{DS} = 10V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	44	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	30	—	pF	
Total Gate Charge	Q_g	—	2.3	—	nC	V_{DS} = 10V, I_D = 11.6A
Gate-Source Charge	Q_{gs}	—	0.3	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.5	—	nC	
Turn-On Delay Time	$t_{d(on)}$	—	8	—	ns	V_{DD} = 10V, R_L = 10Ω I_D = 1A, V_{GEN} = 4.5V, R_G = 6Ω
Rise Time	t_r	—	3.8	—		
Turn-Off Delay Time	$t_{d(off)}$	—	19.6	—		
Fall Time	t_f	—	8.3	—		

Notes: 3. Device mounted on FR-4 PCB, or minimum recommended pad layout
4. Repetitive rating, pulse width limited by junction temperature.
5. Short duration pulse test used to minimize self-heating effect.